

NPN Epitaxial Silicon Transistor

KSP₁₀

Features

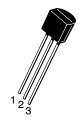
- VHF/UHF Transistor
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS

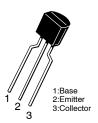
ABSOLUTE MAXIMUM RATINGS

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	3.0	V
PC	Collector Power Dissipation (T _A = 25°C)	350	mW
	Derate above 25°C	2.8	mW/°C
PC	Collector Power Dissipation (T _C = 25°C)	1.0	W
	Derate above 25°C	8.0	W/°C
T_{J}	Junction Temperature	150	°C
T _{STG}	Storage Temperature	–55 to 150	°C
Rth(j-c)	Thermal Resistance, Junction to Case	125	°C/W
Rth(j-a)	Thermal Resistance, Junction to Ambient	357	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

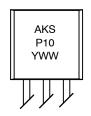




TO-92-3 **CASE 135AN**

TO-92 LF CASE 135AR

MARKING DIAGRAM



= Assembly Code KSP10 = Device Code = Year = Work Week

ORDERING INFORMATION

Device	Package	Shipping
KSP10BU	TO-92 3 (Pb-Free)	10000 / Bulk Bag
KSP10TA	TO-92 3 LF (Pb-Free)	2000 / Fan-Fold

KSP₁₀

ELECTRICAL CHARACTERISTICS (Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	30	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1 mA, I _B = 0	25	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	3.0	_	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 25 \text{ V}, I_{E} = 0$	-	100	nA
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 2 \text{ V}, I_{C} = 0$	-	100	nA
h _{FE}	DC Current Gain	V _{CE} = 10 V, I _C = 4 mA	60	_	-
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 4 mA, I _B = 0.4 mA	-	0.5	V
V _{BE(on)}	Base-Emitter On Voltage	$V_{CE} = 10 \text{ V, I}_{C} = 4 \text{ mA}$	-	0.95	V
f _T	Current Gain Bandwidth Product	V _{CE} = 10 V, I _C = 4 mA, f = 100 MHz	650	_	MHz
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	0.7	pF
Crb	Collector Base Feedback Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	0.35	0.65	pF
C _{c·rbb′}	Collector Base Time Constant	$V_{CB} = 10 \text{ V}, I_{C} = 4 \text{ mA}, f = 31.8 \text{ MHz}$	-	9.0	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: $PW \le 300 \ \mu s$, Duty Cycle $\le 2\%$.

KSP10

TYPICAL CHARACTERISTICS

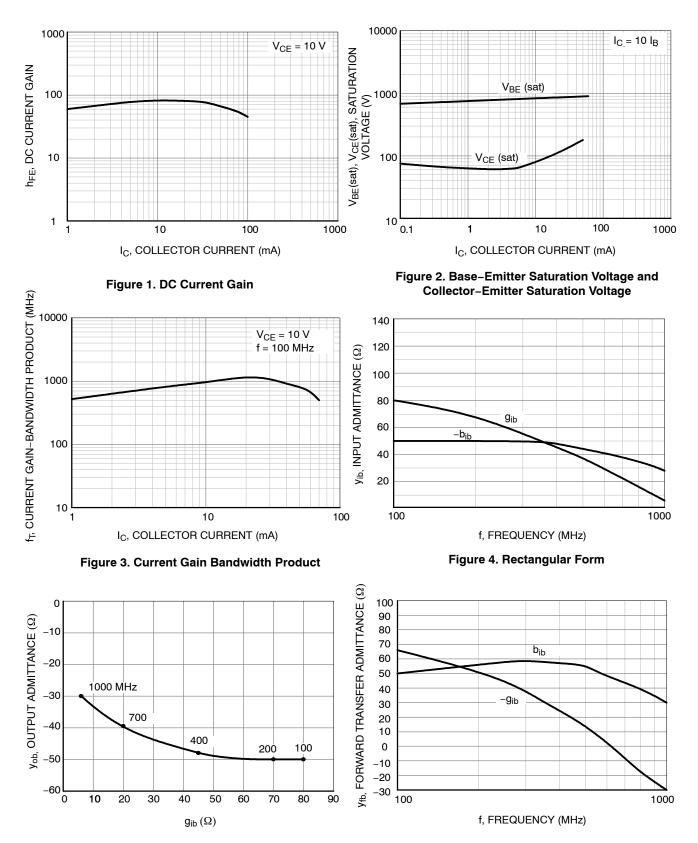


Figure 5. Polar Form

Figure 6. Rectangular Form

KSP10

TYPICAL CHARACTERISTICS (CONTINUED)

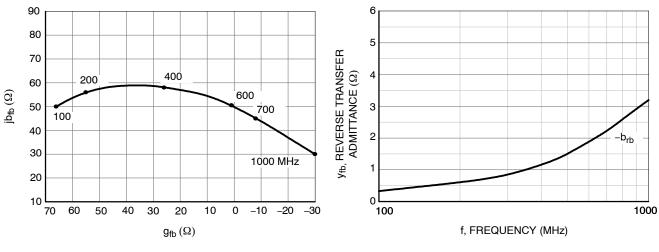


Figure 7. Polar Form

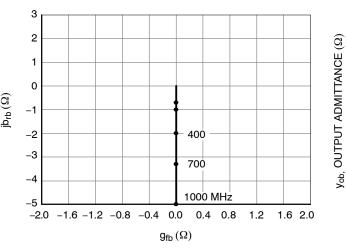


Figure 9. Polar Form

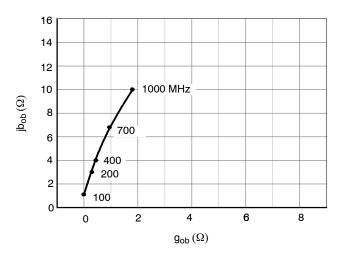


Figure 11. Polar Form



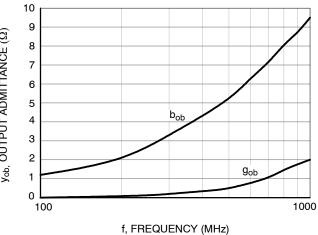
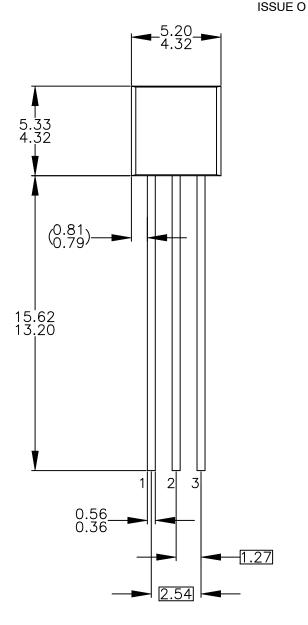
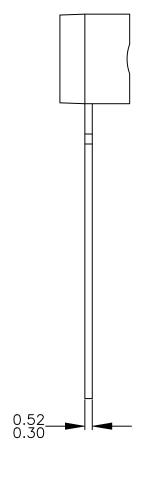


Figure 10. Rectangular Form

TO-92 3 4.825x4.76 CASE 135AN

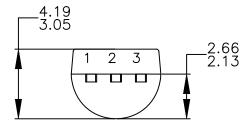
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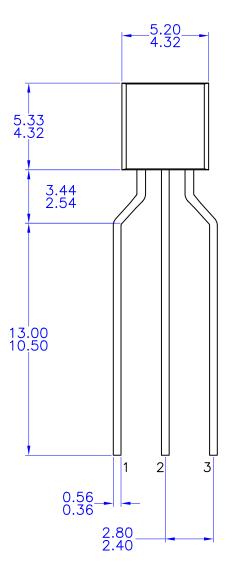
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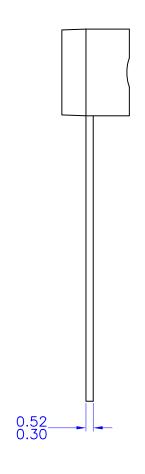
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TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

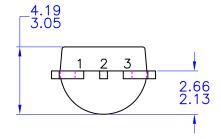
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